

2MBI100XAA170-50

IGBT Modules

Power Module (X series)
1700V / 100A / 2-in-1 package

■ Features

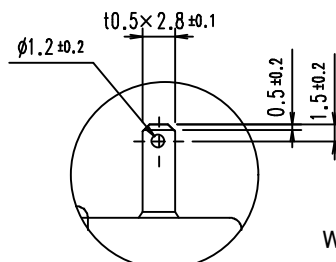
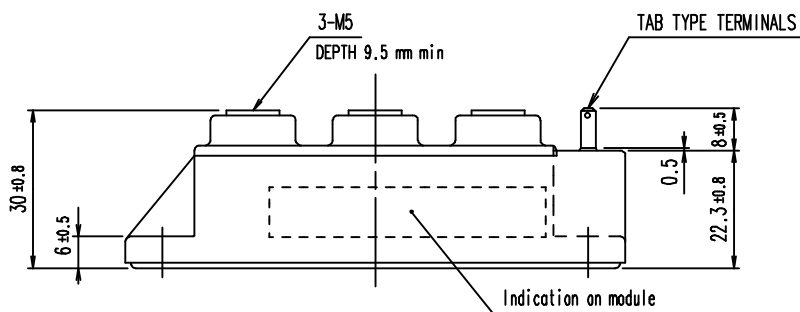
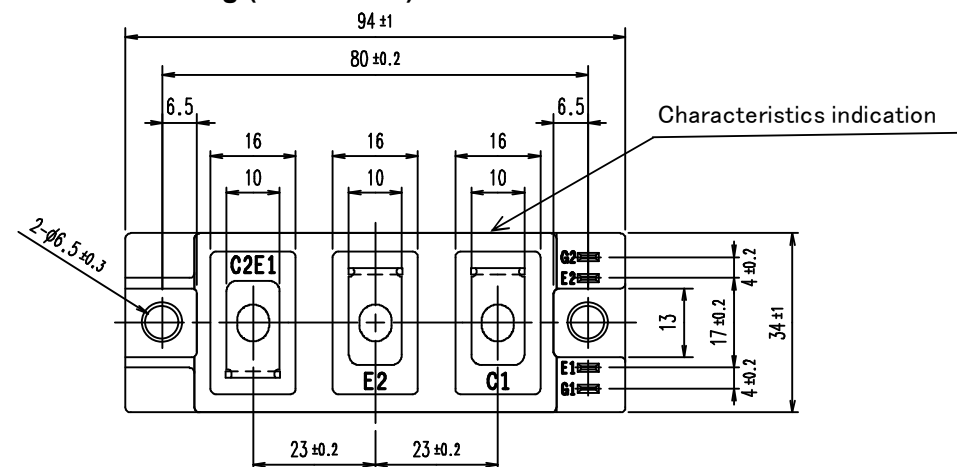
- Low $V_{CE(sat)}$
- High speed switching
- Low Inductance Module structure

■ Applications

- Inverter for Motor Drives, AC and DC Servo Drives
- Uninterruptible Power Supply Systems,
- Industrial machines, such as Welding machines



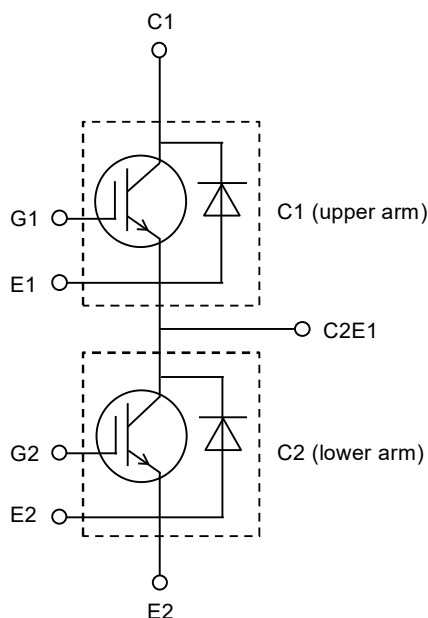
■ Outline drawing (Unit : mm)



Weight: 180 g(typ.)

DETAIL TAB TYPE TERMINALS

■ Equivalent circuit



2MBI100XAA170-50

IGBT Modules

■ Absolute maximum ratings (at $T_c = 25^\circ\text{C}$ unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units
Collector-Emitter voltage, Gate-Emitter short-circuited		V_{CES}			1700	V
Gate-Emitter voltage, Collector-Emitter short-circuited		V_{GES}			± 20	V
Collector current		I_C	Continuous	$T_c = 100^\circ\text{C}$	100	A
Repetitive peak collector current		I_{CRM}	1ms		200	
Forward current		I_F	Continuous		100	
Repetitive peak forward current		I_{FRM}	1ms		200	
Total power dissipation		P_{tot}	1 device		560	W
Virtual junction temperature		T_{vj}			175	$^\circ\text{C}$
Operating virtual junction temperature		T_{vjop}			175	
Case temperature		T_c			125	
Storage temperature		T_{stg}			-40 ~ 125	
Isolation voltage	Between terminals and copper base (*1)	V_{isol}	AC: 1min.		4000	Vrms
Mounting torque of screws to heatsink		M_s	M5 or M6		3.0 ~ 5.0	N·m
Mounting torque of screws to terminals		M_t	M5		2.5 ~ 5.0	

(*1) All terminals should be connected together during the test.

2MBI100XAA170-50

IGBT Modules

■ Electrical characteristics (at $T_{vj} = 25^\circ\text{C}$ unless otherwise specified)

	Symbols	Conditions		Characteristics			Units
				min.	typ.	max.	
Collector-Emitter cut-off current, Gate-Emitter short-circuited	I_{CES}	$V_{GE} = 0V$ $V_{CE} = 1700V$		-	-	50	μA
Gate leakage current, Collector-Emitter short-circuited	I_{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$		-	-	100	nA
Gate-Emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = 20V$ $I_C = 100mA$		6.0	6.5	7.0	V
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15V$ $I_C = 100A$	$T_{vj}=25^{\circ}C$	-	1.70	2.15	V
	$V_{CE(sat)}$ (chip)		$T_{vj}=25^{\circ}C$	-	1.65	2.10	
			$T_{vj}=125^{\circ}C$	-	2.00	-	
			$T_{vj}=150^{\circ}C$	-	2.10	-	
			$T_{vj}=175^{\circ}C$	-	2.20	-	
Internal gate resistance	r_g	-		-	12.50	-	Ω
Capacitance	C_{ies}	$V_{CE}=10V, V_{GE}=0V, f=1MHz$		-	14	-	nF
	C_{oes}			-	0.4	-	
	C_{res}			-	0.08	-	
Gate charge	Q_G	$V_{CC} = 900V, I_C = 100A$ $V_{GE} = -15 \rightarrow +15V$		-	800	-	nC
Forward voltage	V_F (terminal)	$V_{GE} = 0V$ $I_F = 100A$	$T_{vj}=25^{\circ}C$	-	1.75	2.20	V
	V_F (chip)		$T_{vj} = 25^{\circ}C$	-	1.70	2.15	
			$T_{vj}=125^{\circ}C$	-	1.85	-	
			$T_{vj}=150^{\circ}C$	-	1.85	-	
			$T_{vj}=175^{\circ}C$	-	1.80	-	
Switching time (*1)	$t_{d(on)}$	$V_{CC} = 900V$ $I_C, I_F = 100A$ $V_{GE} = \pm 15V$ $R_G = 3.3 \Omega$ $L_S = 30 nH$	$T_{vj} = 25^{\circ}C$	-	405	-	nS
			$T_{vj}=125^{\circ}C$	-	440	-	
			$T_{vj}=150^{\circ}C$	-	450	-	
			$T_{vj}=175^{\circ}C$	-	460	-	
	t_r		$T_{vj} = 25^{\circ}C$	-	70	-	
			$T_{vj}=125^{\circ}C$	-	85	-	
			$T_{vj}=150^{\circ}C$	-	90	-	
			$T_{vj}=175^{\circ}C$	-	90	-	
	$t_{d(off)}$		$T_{vj} = 25^{\circ}C$	-	420	-	
			$T_{vj}=125^{\circ}C$	-	500	-	
			$T_{vj}=150^{\circ}C$	-	500	-	
			$T_{vj}=175^{\circ}C$	-	500	-	
	t_f		$T_{vj} = 25^{\circ}C$	-	465	-	
			$T_{vj}=125^{\circ}C$	-	635	-	
			$T_{vj}=150^{\circ}C$	-	665	-	
			$T_{vj}=175^{\circ}C$	-	750	-	
Reverse recovery time	t_{rr}	$T_{vj} = 25^{\circ}C$	-	820	-		
		$T_{vj}=125^{\circ}C$	-	1285	-		
		$T_{vj}=150^{\circ}C$	-	1390	-		
		$T_{vj}=175^{\circ}C$	-	1500	-		

(*1) Turn-on time (t_{on}) = $t_{d(on)} + t_r$, Turn-off time (t_{off}) = $t_{d(off)} + t_f$

2MBI100XAA170-50

IGBT Modules

■ Electrical characteristics (at $T_{vj} = 25^{\circ}\text{C}$ unless otherwise specified)

Items	Symbols	Conditions		Characteristics			Units
				min.	typ.	max.	
Switching loss (per pulse)	E_{on}	$V_{\text{CC}} = 900\text{V}$ $I_{\text{C}}, I_{\text{F}} = 100\text{A}$ $V_{\text{GE}} = \pm 15\text{V}$ $R_{\text{G}} = 3.3\ \Omega$ $L_{\text{S}} = 30\ \text{nH}$	$T_{\text{vj}} = 25^{\circ}\text{C}$	-	21.8	-	mJ
			$T_{\text{vj}} = 125^{\circ}\text{C}$	-	27.8	-	
			$T_{\text{vj}} = 150^{\circ}\text{C}$	-	29.5	-	
			$T_{\text{vj}} = 175^{\circ}\text{C}$	-	30.6	-	
	E_{off}		$T_{\text{vj}} = 25^{\circ}\text{C}$	-	21.4	-	
			$T_{\text{vj}} = 125^{\circ}\text{C}$	-	28.0	-	
			$T_{\text{vj}} = 150^{\circ}\text{C}$	-	29.6	-	
			$T_{\text{vj}} = 175^{\circ}\text{C}$	-	30.8	-	
	E_{rr}		$T_{\text{vj}} = 25^{\circ}\text{C}$	-	11.8	-	
			$T_{\text{vj}} = 125^{\circ}\text{C}$	-	20.8	-	
			$T_{\text{vj}} = 150^{\circ}\text{C}$	-	24.1	-	
			$T_{\text{vj}} = 175^{\circ}\text{C}$	-	27.7	-	

NOTICE:

The external gate resistance (R_G) shown above is one of our recommended value for the purpose of minimum switching loss. However the optimum R_G depends on circuit configuration and/or environment.

We recommend that the R_G has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

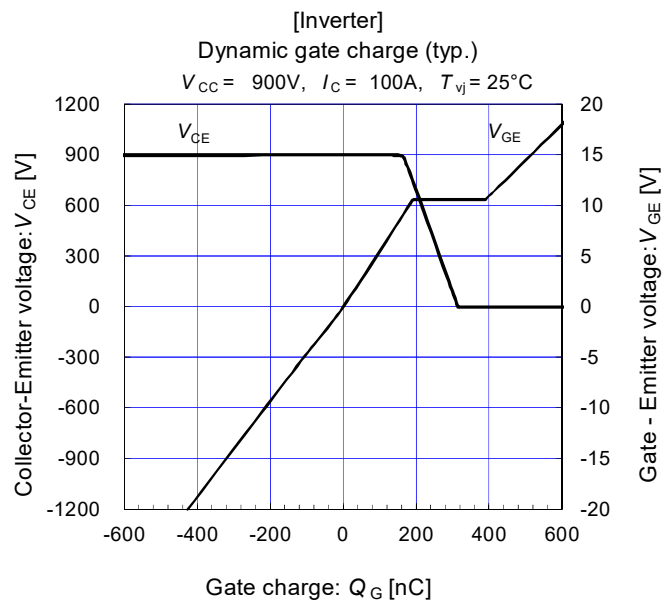
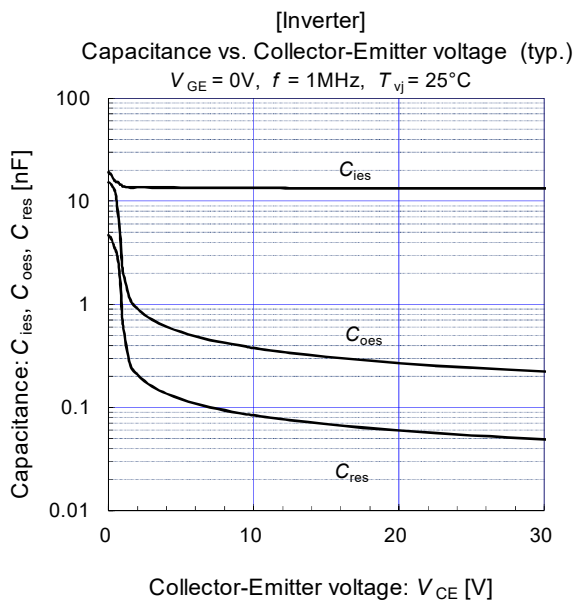
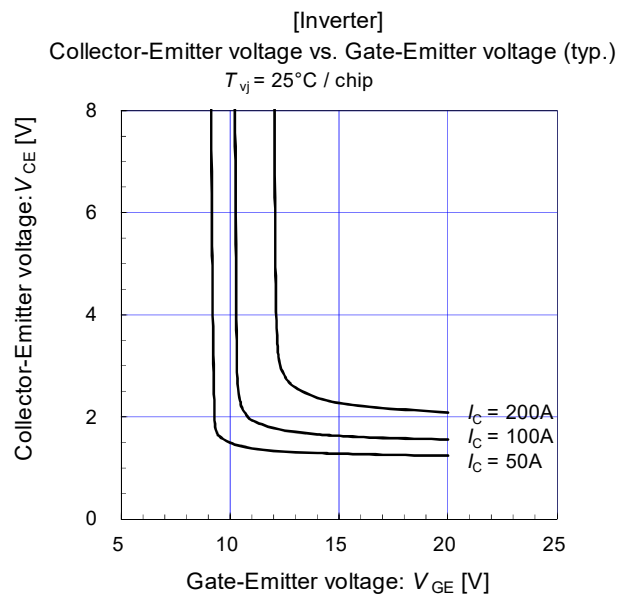
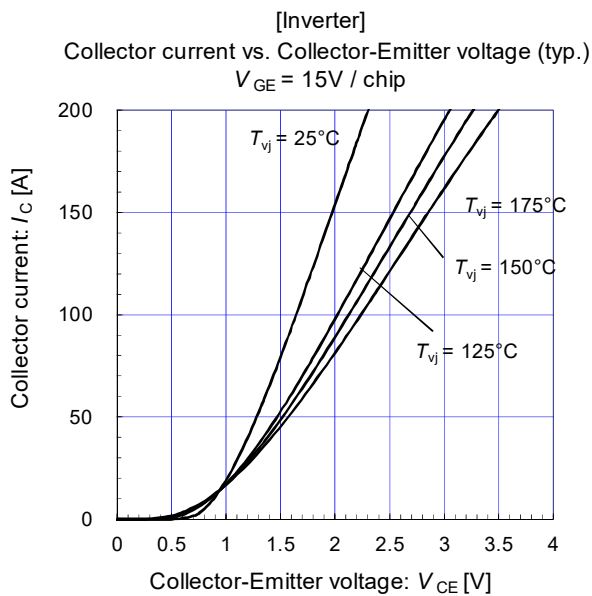
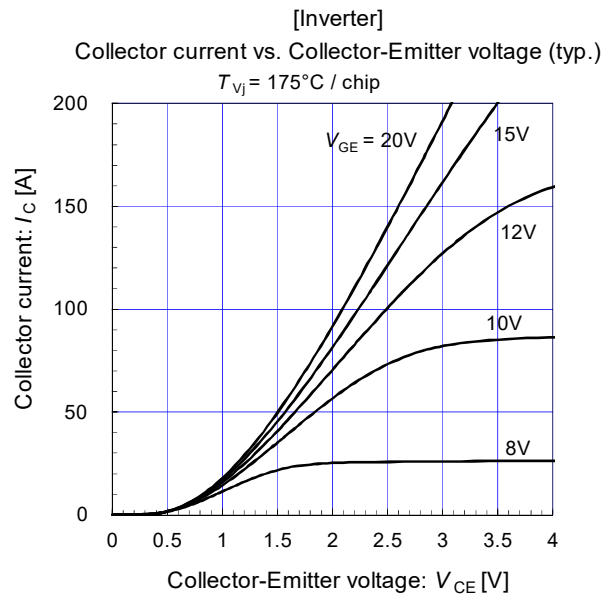
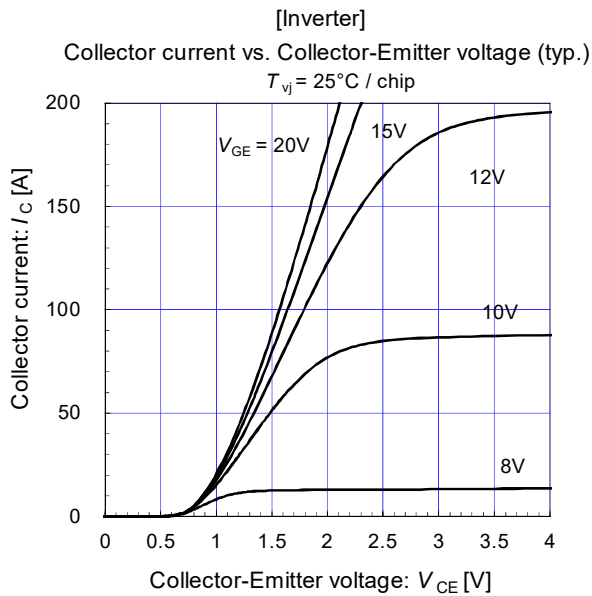
■ Thermal resistance characteristics

	Symbols	Conditions	Characteristics			ns
			min.	typ.	max.	
Thermal resistance (1device)	$R_{th(j-c)}$	Inverter IGBT	-	-	0.266	K/W
		Inverter FWD	-	-	0.446	
Thermal resistance case to heatsink (1IGBT + 1FWD) (*1)	$R_{th(c-s)}$	with 1 W/(m·K) thermal grease	-	0.050	-	

(*1) This is the value which is defined mounting on the additional heatsink with thermal grease.

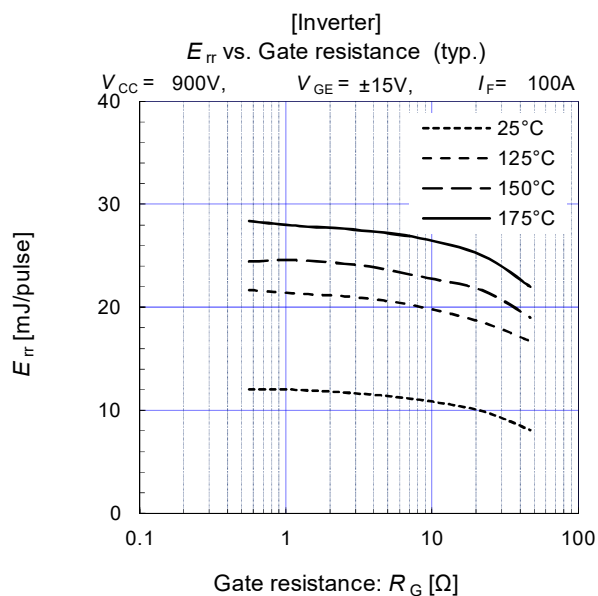
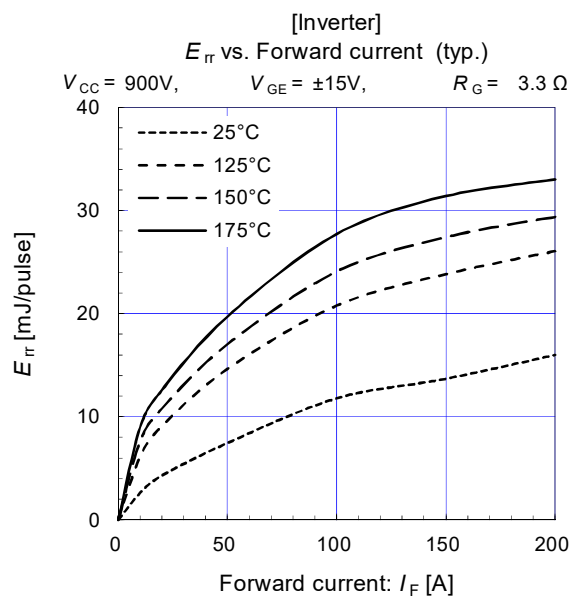
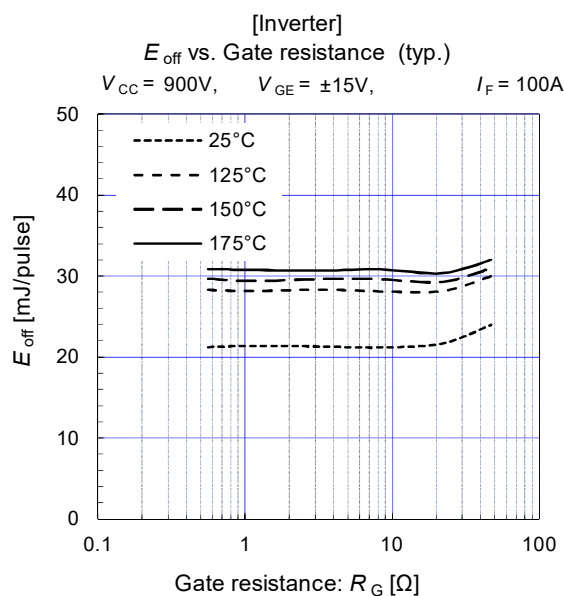
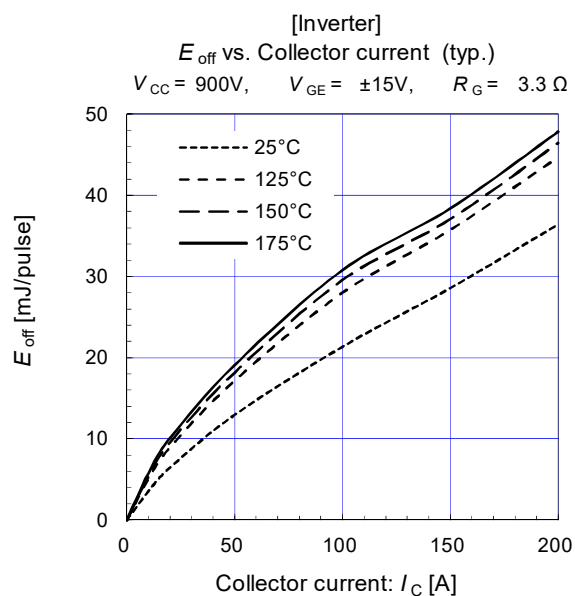
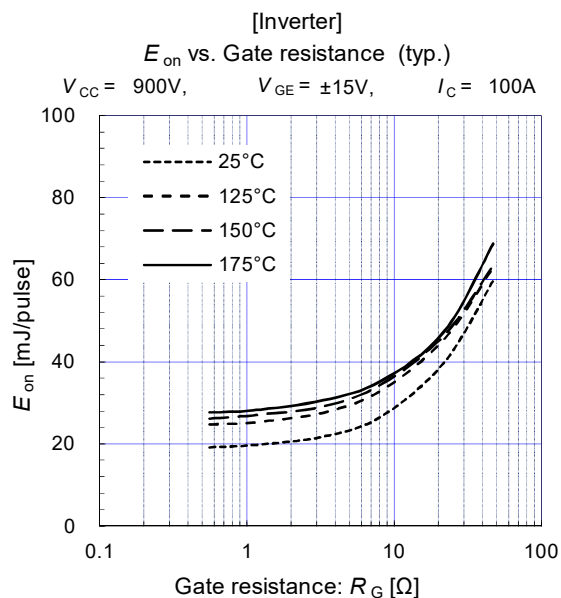
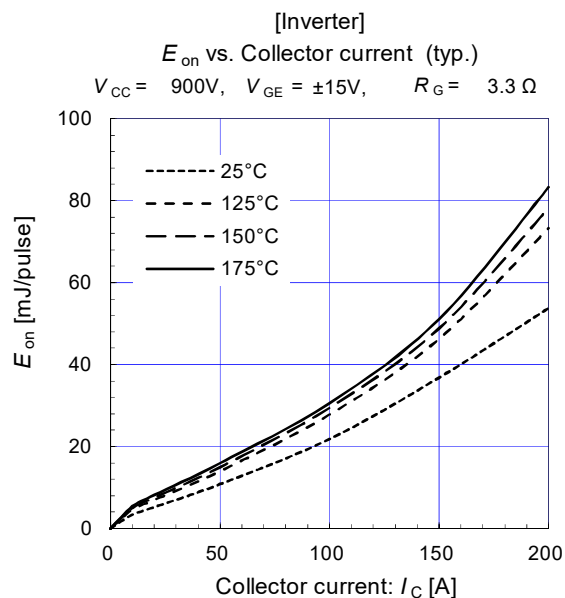
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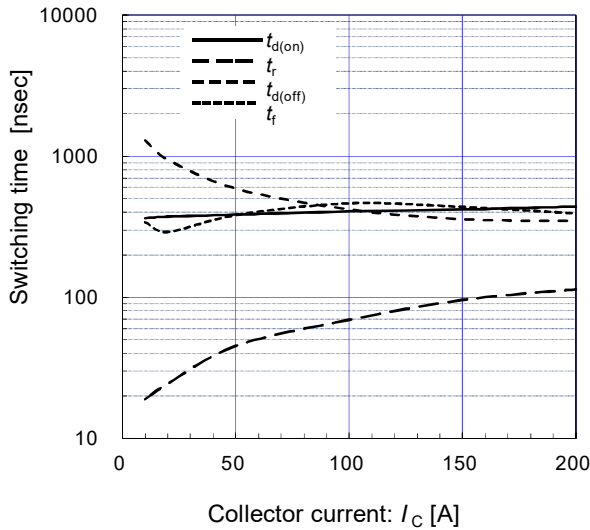
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[Inverter]

Switching time vs. Collector current (typ.)

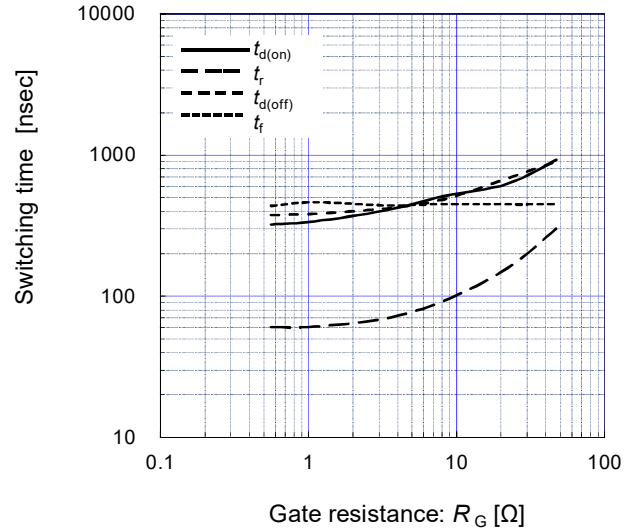
$V_{CC} = 900V$, $R_G = 3.3\ \Omega$, $V_{GE} = \pm 15V$, $T_{vj} = 25^\circ C$



[Inverter]

Switching time vs. Gate resistance (typ.)

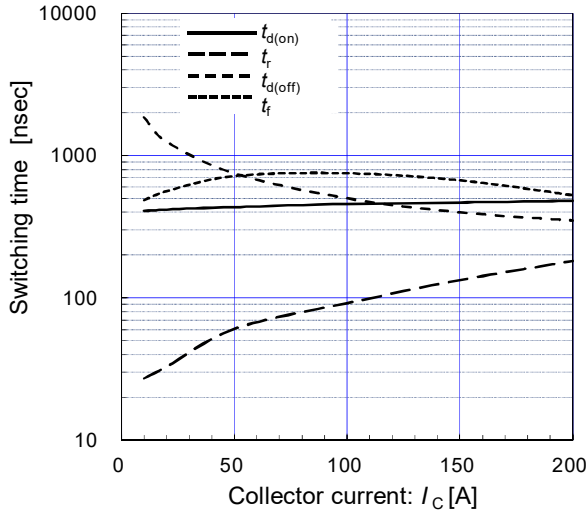
$V_{CC} = 900V$, $I_C = 100A$, $V_{GE} = \pm 15V$, $T_{vj} = 25^\circ C$



[Inverter]

Switching time vs. Collector current (typ.)

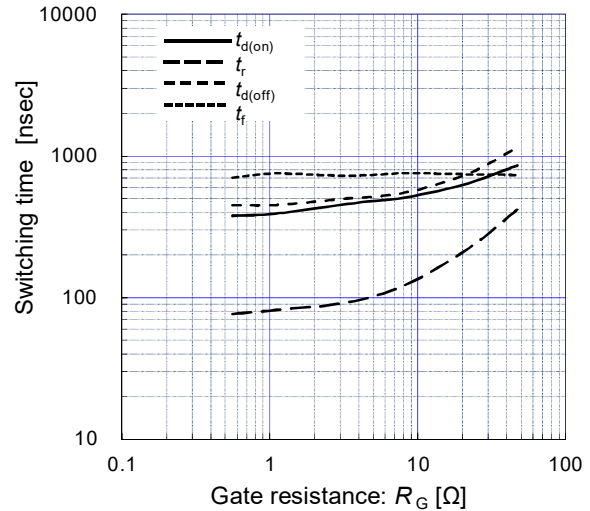
$V_{CC} = 900V$, $R_G = 3.3\ \Omega$, $V_{GE} = \pm 15V$, $T_{vj} = 175^\circ C$



[Inverter]

Switching time vs. Gate resistance (typ.)

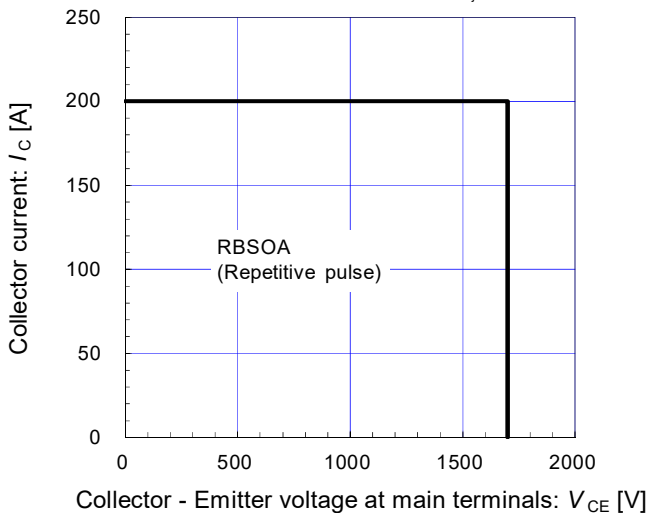
$V_{CC} = 900V$, $I_C = 100A$, $V_{GE} = \pm 15V$, $T_{vj} = 175^\circ C$



[Inverter]

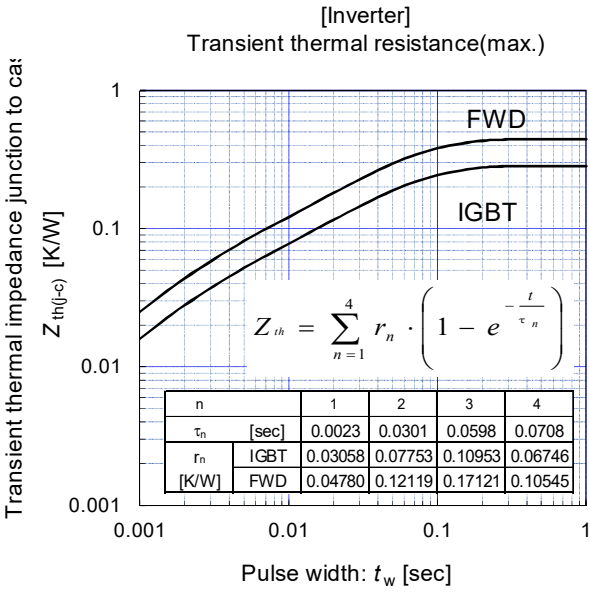
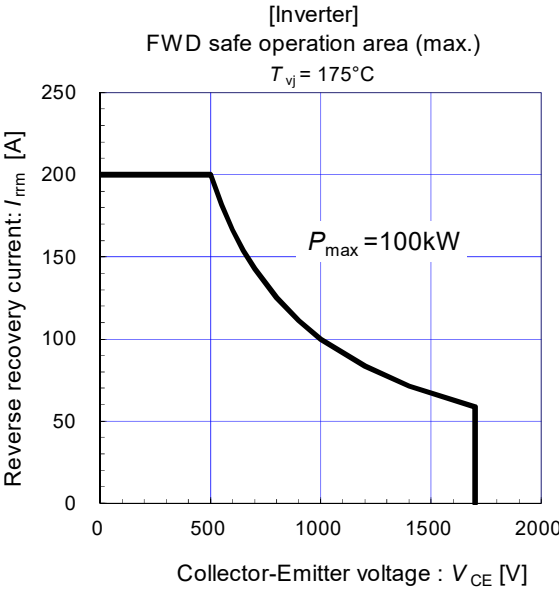
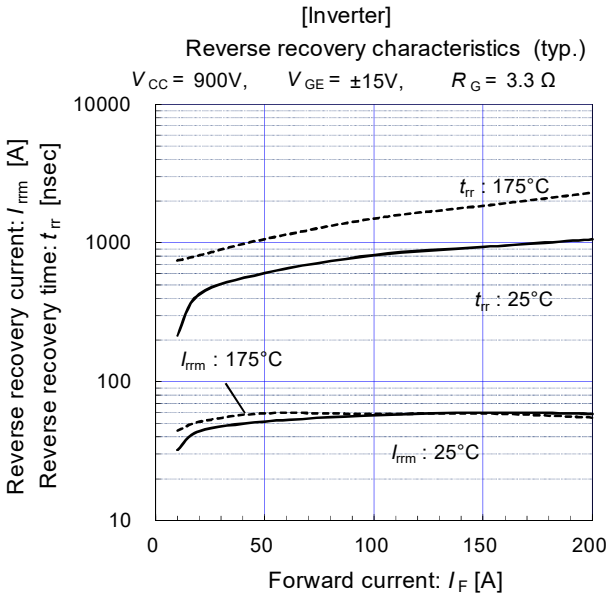
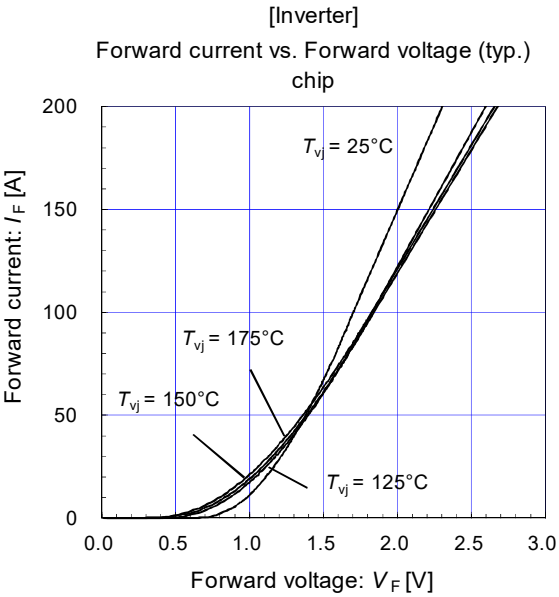
Reverse bias safe operating area (max.)

$V_{GE} = \pm 15V$, $R_G = 3.3\ \Omega$, $T_{vj} = 175^\circ C$



2MBI100XAA170-50

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